RICOH

R3132x/R3133x SERIES

LOW VOLTAGE DETECTOR WITH BUILT-IN DELAY CIRCUIT

NO.EA-093-160314

OUTLINE

R3132x/R3133x Series are CMOS-based low voltage detector ICs with built-in delay circuit, high detector threshold accuracy, and ultra low supply current, which can operate at low voltage.

These ICs can be used as system reset generators, and each of these ICs consists of a voltage reference, a comparator, resistors for setting voltage detector threshold, an output driver transistor, manual reset circuit, and an output delay generator.

Detector threshold is fixed internally with high accuracy and requires no adjustment. When a supply voltage crosses a setting detector threshold voltage from a high value to a lower value, this IC generates reset signal.

R3132x Series output "L" at its detect, while R3133x Series output "H".

Since each of R3132x/R3133x Series embeds an output delay generator, during a setting 240ms delay time, which is fixed in the IC, this IC keeps the reset condition after they are released. Released conditions are the case when a supply voltage crosses a setting detector threshold voltage from a low value to a higher value, or when this IC is released from manual reset.

Two output types, Nch open drain type and CMOS type, are available.

Since the package for these ICs are ultra small SC-82AB package and SON1612-6, high density mounting of the ICs on board is possible.

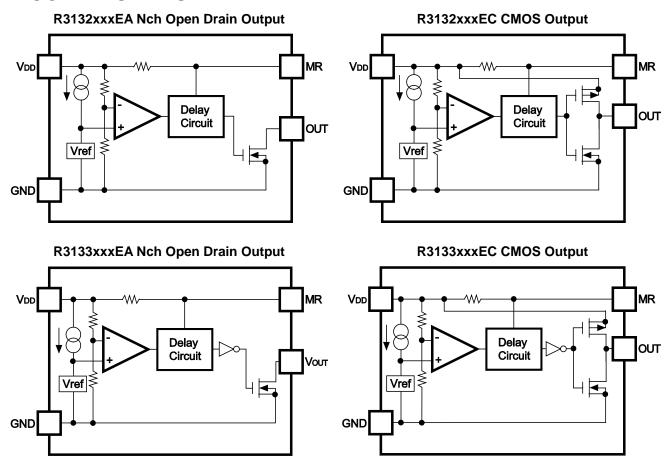
FEATURES

Supply current	Τyp. 0.8μA (R313xx27x: Vpp=3.0V)
Operating Voltage Range	0.8V to 6.0V (Topt=25°C)
Detector Threshold	Setting with a step of 0.1V in the range of 1.0V
	to 5.0V is possible. Further, 2.32V, 2.63V, 2.93V,
	3.08V, 4.38V, and 4.63V can be provided as
	standard.
Embedded Power on Reset Delay Time Circuit	Typ. 240ms
Detector Threshold Accuracy	±2.0%
Released Delay Time Accuracy	±15.0%
Temperature-Drift Coefficient of Detector Threshold	Typ. ±100ppm/°C
Output Types	Nch Open Drain and CMOS
Packages	SC-82AB, SON1612-6

APPLICATIONS

- · CPU and Logic Circuit Reset
- · Battery Checker
- Window Comparator
- Wave Shaping Circuit
- · Battery Back-up Circuit
- · Power Failure Detector

BLOCK DIAGRAMS



SELECTION GUIDE

The package type, the detector threshold, the output type and the taping type for the ICs can be selected at the users' request.

Product Name	Package	Quantity per Reel	Pb Free	Halogen Free
R3132DxxE*(y)-TR-FE R3133DxxE*(y)-TR-FE	SON1612-6	4,000 pcs	Yes	Yes
R3132QxxE*(y)-TR-FE R3133QxxE*(y)-TR-FE	SC-82AB	3,000 pcs	Yes	Yes

xx: The detector threshold can be designated in the range from 1.0V(10) to 5.0V(50) in 0.1V steps.

(2.32V, 2.63V, 2.93V, 3.08V, 4.38V, 4.63V)

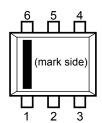
Ex. If the detector threshold is 2.63V, R3132x26E*3-TR-FE.

- * : Designation of Output Type
 - (A) Nch Open Drain
 - (C) CMOS

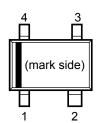
y: If the detector threshold includes the 3rd digit, indicate the digit of 0.01V.

PIN CONFIGURATIONS

• SON1612-6



• SC-82AB



PIN DESCRIPTIONS

• SON1612-6

Pin No	Symbol	Pin Description
1	V _{DD}	Input Pin
2	GND	Ground Pin
3	MR	Manual Reset Input Pin Active at "L" input. Pulled up via $1M\Omega$. If MR pin is not necessary, open this node, or connect to V_{DD} .
4	OUT	Output Pin R3132D Series:"L" at detection R3133D Series:"H" at detection
5	GND	Ground Pin
6	NC	No Connection

• SC-82AB

Pin No	Symbol	Pin Description
1	GND	Ground Pin
2	OUT	Output Pin R3132Q Series :"L" at detection R3133Q Series :"H" at detection
3	MR	Manual Reset Input Pin Active at "L" input. Pulled up via $1M\Omega$. If MR pin is not necessary, open this node, or connect to V_{DD} .
4	V _{DD}	Input Pin

ABSOLUTE MAXIMUM RATINGS

Symbol	Item	Rating	Unit
V _{DD}	Supply Voltage	6.5	V
Vоит	Output Voltage (Nch Open Drain Output)	Vss-0.3 to 6.5	V
VOUT	Output Voltage (CMOS Output)	Vss-0.3 to V _{DD} +0.3	V
Vmr	Input Voltage	Vss-0.3 to V _{DD} +0.3	V
louт	Output Current	20	mA
D	Power Dissipation (SON1612-6)*1, *2	500	ma\A/
P _D	Power Dissipation (SC-82AB)*2	380	mW
Topt	Operating Temperature Range	-40 to 85	°C
Tstg	Storage Temperature Range	-55 to 125	°C
Tsolder	Soldering Temperature	260°C, 10s	

^{*1)} This specification is at mounted on board.

 P_D depends on conditions of mounting on board. This specification is based on the measurement at the condition below:

*Measurement Conditions

Environment: Mounted on board (Wind velocity 0m/s)

Board Material: FR-4 (2-layer)

Board dimensions: 40mm x 40mm x t1.6mm

Copper Area: 50%

*2) For Power Dissipation, please refer to PACKAGE INFORMATION.

ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause the permanent damages and may degrade the life time and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings is not assured.

ELECTRICAL CHARACTERISTICS

Topt=25°C

Symbol	Item	Те	st Conditions	Min.	Тур.	Max.	Unit
		R3132	Topt=25°C	0.75		6.0	
V _{DD}	0	K3132	–40°C≤Topt≤85°C	0.85		6.0	V
V DD	Operating Voltage	R3133	Topt=25°C	0.80		6.0	V
		K3133	–40°C≤Topt≤85°C	0.90		6.0	
VDET	Detector Threshold			V _{DET} × 0.98		V _{DET} × 1.02	V
lss1	Supply Current1	V _{DD} =V _{DET} -0.	1V, Iout=0A			2.0	μΑ
Iss2	Supply Current2	VDD=VDET+0.	1V, Iоυт=0A			2.0	μА
	Supply Current3		V _{DET} <1.6V			3.6	μА
lss3		VDD=6.0V, IOUT=0A	1.6V≤V _{DET} <2.7V			3.0	
		1001-071	2.7V≤V _{DET}			2.5	
Vон	"H" Output Voltage		Refer to the follo	wing tab	le.		
Vol	"L" Output Voltage		Refer to the follo	wing tab	le.		
RMR	MR pin pull-up resistance	Topt=25°C		0.5	1.0	4.0	ΜΩ
Trst*	Output Delay Time for detect	V _{DD} =V _{DET} to V _{DET} -0.1V			15		μS
Tdelay	Output Delay Time for release	VDD=0.8V to VDET+1.0V		204	240	276	ms
$\Delta V_{DET}/\Delta T_{opt}$	Detector Threshold Temperature Coefficient	–40°C≤Topt≤	:85°C		±100		ppm/ °C

^{*)} Guaranteed by design, not mass production tested.

RECOMMENDED OPERATING CONDITIONS (ELECTRICAL CHARACTERISTICS)

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if when they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

• "H" Output Voltage (Voн) table

Topt=25°C

Products	Те	st Conditions	Min.	Тур.	Max.	Unit
	V _{DET} <1.2V	$V_{DD}=V_{DET}+0.1V$, $I_{OH}=-50\mu A$				
R3132xxxEC	1.2V≤V _{DET} <2.0V	V _{DD} =V _{DET} +0.1V, I _{OH} =-150μA	0.0.1/			V
R3132XXXEC	2.0V≤V _{DET} <3.1V	V _{DD} =V _{DET} +0.1V, I _{OH} =-500μA	0.8×V _{DD}			V
	3.1V≤V _{DET}	V _{DD} =V _{DET} +0.1V, I _{OH} =-800μA				
	V _{DET} <1.2V	VDD=VDET-0.1V, IOH=-10μA				
D2122vovEC	1.2V≤V _{DET} <2.0V	V _{DD} =V _{DET} -0.1V, I _{OH} =-100μA	0.0.1/			V
R3133xxxEC	2.0V≤V _{DET} <3.1V	VDD=VDET-0.1V, IOH=-500μA	0.8×V _{DD}			V
	3.1V≤V _{DET}	VDD=VDET-0.1V, IOH=-800μA				

VDET is a set value.

• "L" Output Voltage (Vol) table

Topt=25°C

Symbol	Item	Test Conditions	Min.	Тур.	Max.	Unit
	V _{DET} <1.2V	VDD=VDET-0.1V, IOL=20μA				
R3132xxxEx	1.2V≤V _{DET} <1.6V	VDD=VDET-0.1V, IOL=750μA			0.3	V
R3132XXXEX	1.6V≤V _{DET} <3.1V	VDD=VDET-0.1V, IOL=1.2mA				
	3.1V≤V _{DET}	VDD=VDET-0.1V, IOL=3.2mA			0.4	V
	V _{DET} <1.2V	Vdd=Vdet+0.1V, Iol=20μA				
D2122vovEv	1.2V≤V _{DET} <1.6V	VDD=VDET+0.1V, IOL=750μA			0.3	V
R3133xxxEx	1.6V≤V _{DET} <3.1V	VDD=VDET+0.1V, IOL=1.2mA				
	3.1V≤V _{DET}	VDD=VDET+0.1V, IOL=3.2mA			0.4	V

VDET is a set value.

DETECTOR THRESHOLD SPECIFICATIONS BY PART NUMBER

• R3132x

		Operati	ing Voltage		Detec	tor Thre	shold	Supply C	urrent 1	
Part Number		٧	DD[V]			VDET[V]		Iss1[μ A]	
	Conditions	Min.	Conditions	Min.	Min.	Тур.	Max.	Conditions	Тур.	Max.
R3132x23Ex2	_				2.274	2.320	2.366		0.8	
R3132x26Ex3	_				2.578	2.630	2.682		0.0	
R3132x29Ex3	Topt=25°C	0.75	–40°C≤Topt≤85°C	0.85	2.872	2.930	2.988	VDD=VDET-0.1V		2.0
R3132x30Ex8	Τορι-25 Ο	0.75	-40 O=10pt=00 O	0.00	3.019	3.080	3.141	Iout=0A	0.9	2.0
R3132x43Ex8					4.293	4.380	4.467		0.5	
R3132x46Ex3					4.538	4.630	4.722			
R3132x10Ex					0.980	1.000	1.020			
R3132x11Ex					1.078	1.100	1.122			
R3132x12Ex					1.176	1.200	1.224			
R3132x13Ex	_				1.274	1.300	1.326			
R3132x14Ex	_				1.372	1.400	1.428			
R3132x15Ex					1.470	1.500	1.530			
R3132x16Ex	_				1.568	1.600	1.632			
R3132x17Ex					1.666	1.700	1.734			
R3132x18Ex					1.764	1.800	1.836		0.8	
R3132x19Ex					1.862	1.900	1.938			
R3132x20Ex					1.960	2.000	2.040			
R3132x21Ex					2.058	2.100	2.142			
R3132x22Ex					2.156	2.200	2.244			
R3132x23Ex					2.254	2.300	2.346			
R3132x24Ex					2.352	2.400	2.448			
R3132x25Ex					2.450	2.500	2.550			
R3132x26Ex					2.548	2.600	2.652			
R3132x27Ex					2.646	2.700	2.754			
R3132x28Ex					2.744	2.800	2.856			
R3132x29Ex					2.842	2.900	2.958	\/ \/ 0 4\/		
R3132x30Ex	Topt=25°C	0.75	–40°C≤Topt≤85°C	0.85	2.940	3.000	3.060	VDD=VDET-0.1V IOUT=0A		2.0
R3132x31Ex					3.038	3.100	3.162	1001= 0A		
R3132x32Ex					3.136	3.200	3.264			
R3132x33Ex					3.234	3.300	3.366			
R3132x34Ex					3.332	3.400	3.468			
R3132x35Ex					3.430	3.500	3.570			
R3132x36Ex					3.528	3.600	3.672			
R3132x37Ex					3.626	3.700	3.774			
R3132x38Ex					3.724	3.800	3.876		0.9	
R3132x39Ex					3.822	3.900	3.978		0.9	
R3132x40Ex					3.920	4.000	4.080			
R3132x41Ex					4.018	4.100	4.182			
R3132x42Ex					4.116	4.200	4.284			
R3132x43Ex					4.214	4.300	4.386			
R3132x44Ex					4.312	4.400	4.488			
R3132x45Ex					4.410	4.500	4.590			
R3132x46Ex					4.508	4.600	4.692			
R3132x47Ex					4.606	4.700	4.794			
R3132x48Ex					4.704	4.800	4.896			
R3132x49Ex					4.802	4.900	4.998			
R3132x50Ex	1				4.900	5.000	5.100	1		

Supply Cu	ırrent 2		Supply C	Surrent 3	1	"H" Output Volt	age
Iss2[µ	Α]		Iss3[μ Α]		VoH[V]	
Conditions	Тур.	Max.	Conditions	Тур.	Max.	Conditions	Min.
VDD=VDET+0.1V	0.8	2.0	VDD=6.0V	1.2	3.0	Vdd=Vdet+0.1V Ioh=-500μA	0.8×
Iout=0A		2.0	Іоит=0А	1.0	2.5	VDD=VDET+0.1V IOH=-800μA	VDD
						Vdd=Vdet+0.1V Ioн=-50μA	-
					3.6		
				1.4		Vdd=Vdet+0.1V Іон=–150µA	
					3.0		-
				1.2		Vdd=Vdet+0.1V Ioн=–500µA	
VDD=VDET+0.1V IOUT=0A	0.8	2.0	Vdd=6.0V Iout=0A				0.8× VDD
1001-07			1001-0/(1.0	2.5	Vdd=Vdet+0.1V Ioн=–800µA	VSD
				0.8			

	"L" Output Vo	oltage	MR pin "H" Voltage		MR pin "L" I Voltage		MR pin p	ull-up re	esistanc	e		
Part Number	Vol[V]		VIH[V]		Vı∟[V]			RMR[MΩ]			
	Conditions	Max.	Conditions	Min.	Conditions	Max.	Conditions	Min.	Тур.	Max.		
R3132x23Ex2												
R3132x26Ex3	VDD=VDET-0.1V	0.0										
R3132x29Ex3	IoL=+1.2mA	0.3	\/>\/ 0.4	0.75×	\/>\/ 0.4	0.2×	T 0500	0.5	4.0	4.0		
R3132x30Ex8			VDD≥VDET+0.1	VDD	VDD≥VDET+0.1	Vdd	Topt=25°C	0.5	1.0	4.0		
R3132x43Ex8	VDD=VDET-0.1V	0.4										
R3132x46Ex3	IoL=+3.2mA	0.4										
R3132x10Ex	VDD=VDET-0.1V											
R3132x11Ex	Iol=+20μA											
R3132x12Ex												
R3132x13Ex	VDD=VDET-0.1V											
R3132x14Ex	IoL=+750μA											
R3132x15Ex												
R3132x16Ex												
R3132x17Ex												
R3132x18Ex												
R3132x19Ex												
R3132x20Ex		0.3										
R3132x21Ex												
R3132x22Ex	., ., ., .,	\(\(\) \(\	\/ \/ 0.4\/									
R3132x23Ex	VDD=VDET-0.1V											
R3132x24Ex	IoL=+1.2mA											
R3132x25Ex												
R3132x26Ex												
R3132x27Ex												
R3132x28Ex												
R3132x29Ex								0.0				
R3132x30Ex			VDD≥VDET+0.1	0.75× V _{DD}	VDD≥VDET+0.1	0.2× Vdd	Topt=25°C	0.5	1.0	4.0		
R3132x31Ex]	VDD		VDD						
R3132x32Ex												
R3132x33Ex												
R3132x34Ex												
R3132x35Ex												
R3132x36Ex												
R3132x37Ex												
R3132x38Ex												
R3132x39Ex												
R3132x40Ex	VDD=VDET-0.1V	0.4										
R3132x41Ex	IoL=+3.2mA	0.4										
R3132x42Ex												
R3132x43Ex												
R3132x44Ex												
R3132x45Ex												
R3132x46Ex												
R3132x47Ex												
R3132x48Ex	1											
R3132x49Ex												
R3132x50Ex												

Output Dela		Detector Thres Temperature Coe	fficient		
	lelay[ms		1	ΔVDET/ΔTopt[pp	
Conditions	Min.	Тур.	Max.	Conditions	Тур.
VDD=0.8V→ VDET+1.0V Topt=25°C	204	240	276	–40°C≤Topt≤85°C	±100
VDD=0.8V→ VDET+1.0V Topt=25°C	204	240	276	-40°C≤Topt≤85°C	±100

• R3133x

		Operati	ing Voltage		Detec	tor Thre	,			
Part Number		٧	DD[V]		VDET[V]			Iss1[μA]		
	Conditions	Min.	Conditions	Min.	Min.	Тур.	Max.	Conditions	Тур.	Max.
R3133x23Ex2					2.274	2.320	2.366		0.0	
R3133x26Ex3					2.578	2.630	2.682		8.0	
R3133x29Ex3	Topt=25°C	0.00	4000 <t+<0500< td=""><td rowspan="3">0.90</td><td>2.872</td><td>2.930</td><td>2.988</td><td rowspan="3">VDD=VDET-0.1V IOUT=0A</td><td rowspan="4">0.9</td><td rowspan="3">2.0</td></t+<0500<>	0.90	2.872	2.930	2.988	VDD=VDET-0.1V IOUT=0A	0.9	2.0
R3133x30Ex8		0.80	–40°C≤Topt≤85°C		3.019	3.080	3.141			
R3133x43Ex8					4.293	4.380	4.467			
R3133x46Ex3					4.538	4.630	4.722			
R3133x10Ex					0.980	1.000	1.020			
R3133x11Ex					1.078	1.100	1.122			
R3133x12Ex					1.176	1.200	1.224			
R3133x13Ex					1.274	1.300	1.326			
R3133x14Ex					1.372	1.400	1.428			
R3133x15Ex					1.470	1.500	1.530			
R3133x16Ex					1.568	1.600	1.632			
R3133x17Ex					1.666	1.700	1.734		0.8	
R3133x18Ex					1.764	1.800	1.836			
R3133x19Ex					1.862	1.900	1.938			
R3133x20Ex					1.960	2.000	2.040			
R3133x21Ex					2.058	2.100	2.142			
R3133x22Ex					2.156	2.200	2.244			
R3133x23Ex					2.254	2.300	2.346			
R3133x24Ex					2.352	2.400	2.448			
R3133x25Ex					2.450	2.500	2.550			
R3133x26Ex					2.548	2.600	2.652			
R3133x27Ex					2.646	2.700	2.754			
R3133x28Ex					2.744	2.800	2.856			
R3133x29Ex					2.842	2.900	2.958			
R3133x30Ex	Topt=25°C	0.80	–40°C≤Topt≤85°C	0.90	2.940	3.000	3.060	VDD=VDET-0.1V		2.0
R3133x31Ex		0.00		0.30	3.038	3.100	3.162	louт=0А		2.0
R3133x32Ex					3.136	3.200	3.264			
R3133x33Ex					3.234	3.300	3.366			
R3133x34Ex					3.332	3.400	3.468			
R3133x35Ex					3.430	3.500	3.570			
R3133x36Ex					3.528	3.600	3.672			
R3133x37Ex					3.626	3.700	3.774			
R3133x38Ex					3.724	3.800	3.876	1		
R3133x39Ex					3.822	3.900	3.978	=	0.9	
R3133x40Ex					3.920	4.000	4.080	1		
R3133x41Ex					4.018		4.182	1		
R3133x42Ex					4.116	4.200	4.284	1		
R3133x43Ex					4.214	4.300	4.386	1		
R3133x44Ex					4.312	4.400	4.488	1		
R3133x45Ex					4.410	4.500	4.590	1		
R3133x46Ex					4.508	4.600	4.692	1		
R3133x47Ex					4.606	4.700	4.794	1		
R3133x48Ex					4.704	4.800	4.896	1		
R3133x49Ex					4.802	4.900	4.998	1		
IND IDDA#BEX					4.900	5.000	5.100	1		

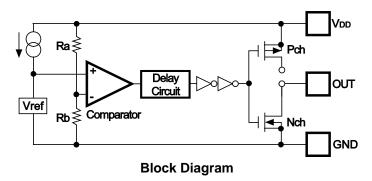
Supply Current 2		Supply (Current 3	"H" Output Voltage				
Iss2[μA]			Issa	[μΑ]	Voн[V]			
Conditions	Тур.	Max.	Conditions	Тур.	Max.	Conditions	Min.	
VDD=VDET+0.1V			VDD=6.0V	1.2	3.0	VDD=VDET-0.1V IOH=-500μA	0.8×	
Iout=0A	8.0	2.0	Іоит=0А	1.0	2.5	VDD=VDET-0.1V IOH=-800μA	VDD	
						VDD=VDET-0.1V IOH=-10μA		
				1.4	3.6	VDD=VDET-0.1V		
	0.8 2.		Vdd=6.0V Iout=0A			VDD=VDE1-0.1V IOH=-100μA	0.8× VDD	
				1.2	3.0	Vdd=Vdet-0.1V Ioh=-500μA		
VDD=VDET+0.1V IOUT=0A		2.0						
				1001-04	IOUT=UA	1.0	2.5	Vdd=Vdet-0.1V Ioh=-800μA
				0.8				

	"L" Output Voltage VoL[V]		MR pin "H" Input Voltage VH[V]		MR pin "L" Input Voltage Vı∟[V]		MR pin pull-up resistance R _{MR} [MΩ]			
Part Number										
	Conditions	Max.	Conditions	Min.	Conditions	Max.	Conditions	Min.	Тур.	Max.
R3133x23Ex2										
R3133x26Ex3	VDD=VDET+0.1V	0.2								
R3133x29Ex3	IoL=+1.2mA	0.3	\/>\/ 0.4	0.75×	., .,,	0.2×	T 1.0500	0.5	1.0	4.0
R3133x30Ex8			VDD≥VDET+0.1	VDD	VDD≥VDET+0.1	Vdd	Topt=25°C	0.5		4.0
R3133x43Ex8	VDD=VDET+0.1V	0.4								
R3133x46Ex3	IoL=+3.2mA	0.4								
R3133x10Ex	VDD=VDET+0.1V									
R3133x11Ex	Iol=+20μA									
R3133x12Ex										
R3133x13Ex	VDD=VDET+0.1V									
R3133x14Ex	IoL=+750μA									
R3133x15Ex										
R3133x16Ex										
R3133x17Ex						0.2× VDD	Topt=25°C	0.5	1.0	4.0
R3133x18Ex										
R3133x19Ex										
R3133x20Ex		0.3								
R3133x21Ex	1									
R3133x22Ex	1	,								
R3133x23Ex	VDD=VDET+0.1V									
R3133x24Ex	loL=+1.2mA									
R3133x25Ex										
R3133x26Ex	1									
R3133x27Ex	1									
R3133x28Ex	1									
R3133x29Ex	1									
R3133x30Ex			VDD≥VDET+0.1	0.75×	VDD≥VDET+0.1					
R3133x31Ex		1	1	Vdd						
R3133x32Ex	1									
R3133x33Ex										
R3133x34Ex										
R3133x35Ex										
R3133x36Ex	1									
R3133x37Ex										
R3133x38Ex										
R3133x39Ex	7									
R3133x40Ex	VDD=VDET+0.1V IOL=+3.2mA	•								
R3133x41Ex		0.4								
R3133x42Ex										
R3133x43Ex										
R3133x44Ex										
R3133x45Ex										
R3133x46Ex										
R3133x47Ex										
R3133x48Ex										
R3133x49Ex	╡									
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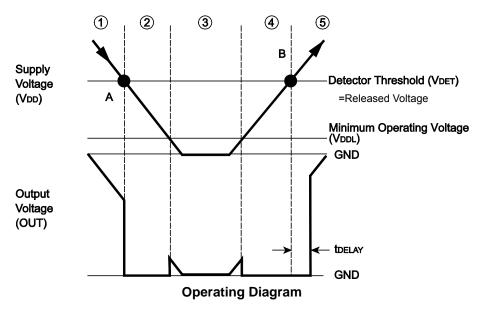
Output Dela	y Time f	Detector Threshold Temperature Coefficient			
To	lelay[ms	ΔVDET/ΔTopt[pp	m/°C]		
Conditions	Min.	Тур.	Max.	Conditions	Тур.
V _{DD} =0.8V→ V _{DET} +1.0V Topt=25°C	204	240	276	–40°C≤Topt≤85°C	±100
VDD=0.8V→ VDET+1.0V Topt=25°C	204	240	276	–40°C≤Topt≤85°C	±100

OPERATION

Operation of R3132x Series



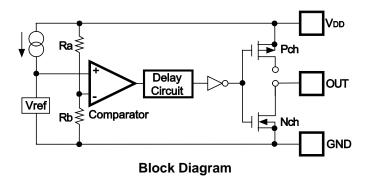
- CMOS Output Type:
 - OUT pin is connected to the drain of Nch Tr. and Pch Tr. in this IC.
- Nch Open Drain Output Type:
 OUT pin is connected to the drain of Nch Tr. in this IC.
 (OUT pin should be pulled up to V_{DD} or an external voltage level.)



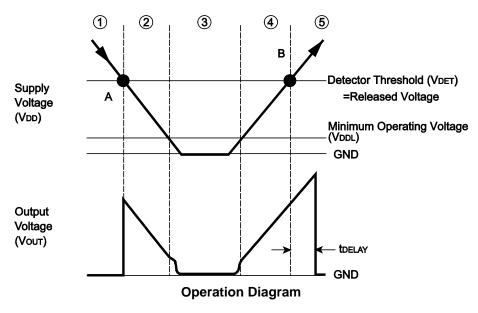
In the above diagram,

- ① Output voltage becomes equal to supply voltage (Nch open drain output type; equal to pull-up Voltage).
- ② When the supply voltage is down to the detector threshold level (Point A), Vref≥V_{DD} × Rb / (Ra+Rb) is true. Then, the output of the comparator is reversed, thus output voltage becomes equal to GND level.
- ③ When the supply voltage is lower than minimum operating voltage, the output of transistor is indefinite, therefore the output is also indefinite.
- ④ Output voltage is equal to GND level.
- ⑤ When the supply voltage is higher than the released voltage (Point B), Vref≤V_{DD} × Rb / (Ra+Rb) is true. Then the output of the comparator is reversed, thus the output voltage becomes equal to the supply voltage (Nch open drain output type; equal to pull-up voltage).
- * There is no hysteresis range between the detector threshold and the released voltage.

Operation of R3133x Series



- CMOS Output Type:
 Out pin is connected to the drain of Nch Tr. and Pch Tr. in this IC.
- Nch Open Drain Output Type:
 Out pin is connected to the drain of Nch Tr. in this IC.
 (OUT pin should be pulled up to V_{DD} or an external voltage level.)

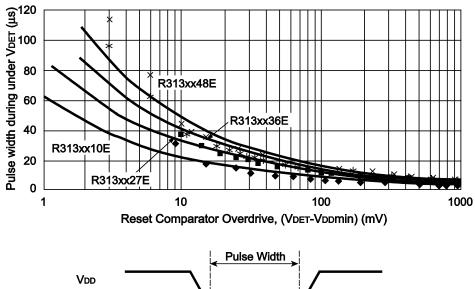


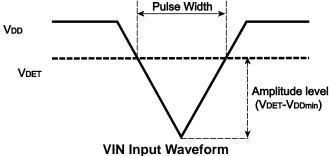
In the above diagram,

- ① Output voltage becomes equal to GND level.
- ② When the supply voltage is down to the detector threshold level (Point A), Vref≥V_{DD} × Rb / (Ra+Rb) is true. Then, the output of the comparator is reversed, thus output voltage becomes equal to the supply voltage (Nch open drain output type; equal to pull-up voltage).
- ③ When the supply voltage is lower than minimum operating voltage, the output of transistor is indefinite, therefore the output is also indefinite. (Nch open drain output type; the output voltage level is equal to pull-up voltage.)
- ④ Output voltage is equal to the supply voltage. (Nch open drain output type; equal to pull-up Voltage.)
- ⑤ When the supply voltage is higher than the released voltage (Point B), Vref≤V_{DD} × Rb / (Ra+Rb) is true. Then the output of the comparator is reversed, thus the output voltage becomes equal to GND level after the output delay time.
- There is no hysteresis range between the detector threshold and the released voltage.

TECHNICAL NOTES

When the IC is released, if a large pulse (glitch) which crosses the detector threshold voltage is in, the IC may not maintain the released condition. The amplitude of the pulse (VDET-VDDmin) and the pulse width the IC can maintain the released level is described in the graph as follows:





Notes:

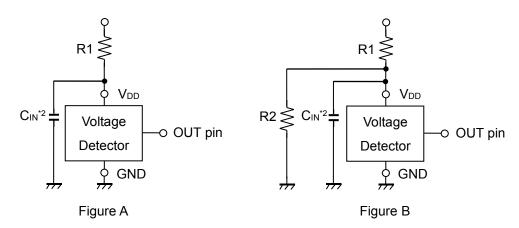
The graph above shows the condition for the maximum transient duration without generating a reset. If the larger amplitude or larger pulse width noise than the graph may be on the V_{DD} , the reset signal may be generated.

When connecting resistors to the device's input pin

When connecting a resistor (R1) to an input of this device, the input voltage decreases by [Device's Consumption Current] x [Resistance Value] only. And, the cross conduction current*1, which occurs when changing from the detecting state to the release state, is decreased the input voltage by [Cross Conduction Current] x [Resistance Value] only. And then, this device will enter the re-detecting state if the input voltage reduction is larger than the difference between the detector voltage and the released voltage.

When the input resistance value is large and the VDD is gone up at mildly in the vicinity of the released voltage, repeating the above operation may result in the occurrence of output.

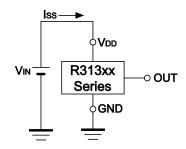
As shown in Figure A/B, set R1 to become 100 k Ω or less as a guide, and connect C_{IN} of 0.1 μ F and more to between the input pin and GND. Besides, make evaluations including temperature properties under the actual usage condition, with using the evaluation board like this way. As a result, make sure that the cross conduction current has no problem.



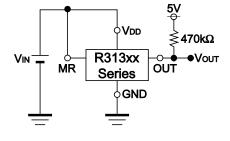
^{*1} In the CMOS output type, a charging current for OUT pin is included.

^{*2} Note the bias dependence of capacitors.

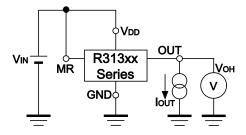
TEST CIRCUITS



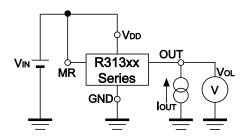
Supply Current Test Circuit



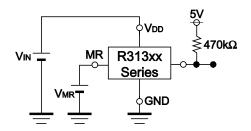
Detector Threshold Test Circuit (CMOS Output type; pull-up part is not necessary.)



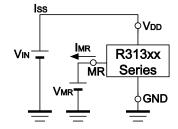
"H" Output Voltage Test Circuit (CMOS Output Type only)



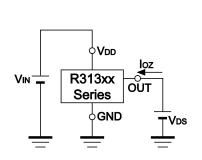
"L" Output Voltage Test Circuit



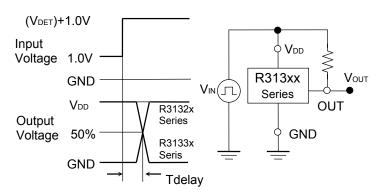
MR pin Input Voltage Test Circuit (CMOS Output type; pull-up part is not necessary.)



MR pin Pull-up Resistance Test Circuit



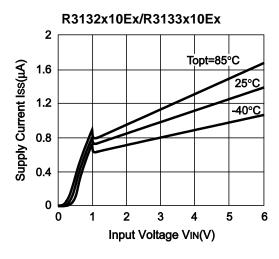
Off Leakage Current Test Circuit

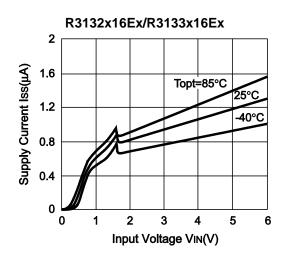


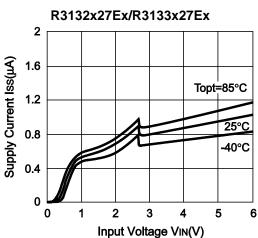
Output Delay Time Test Circuit (CMOS Output type; pull-up is not necessary.)

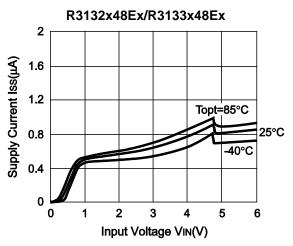
TYPICAL CHARACTERISTICS

1) Supply Current vs. Input Voltage

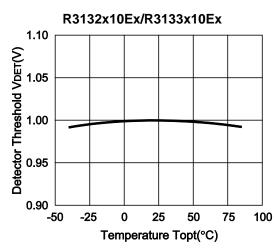


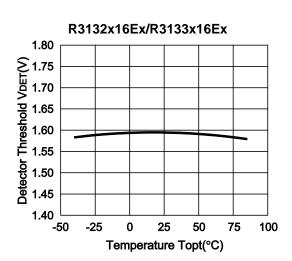


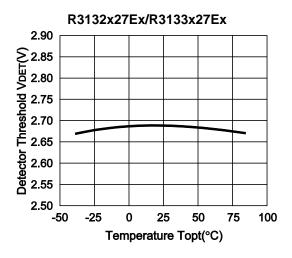


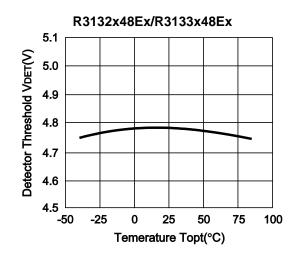


2) Detector Threshold vs. Temperature

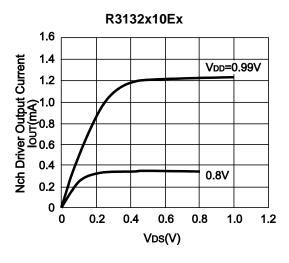


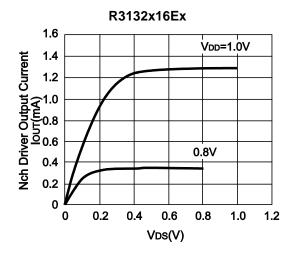


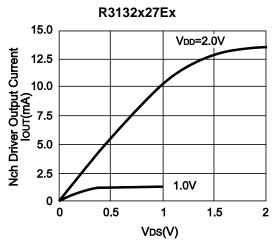


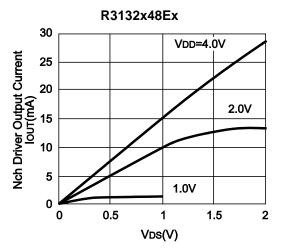


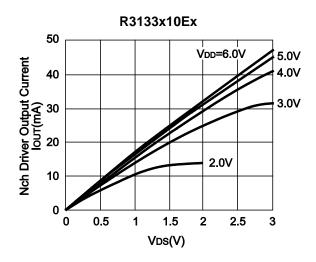
3) Nch Driver Output Current vs. V_{DS} (Topt=25°C)

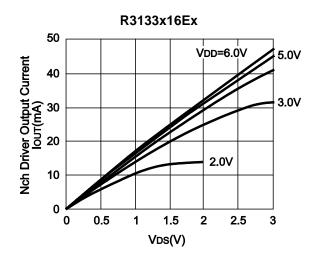


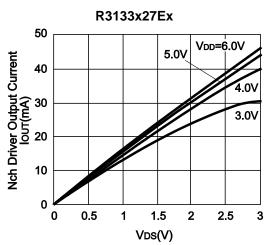


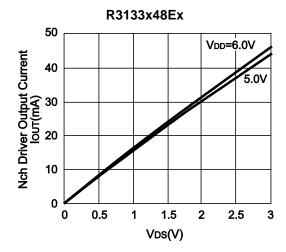




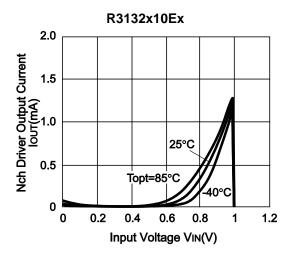


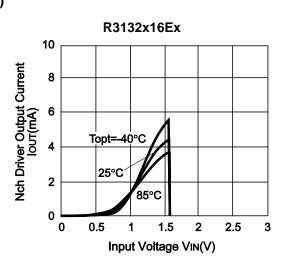


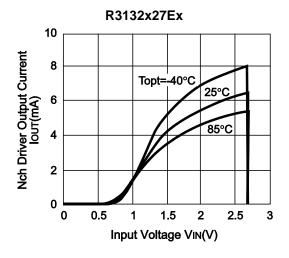


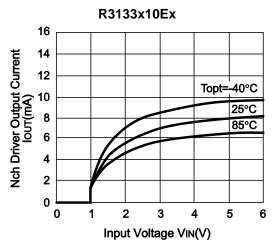


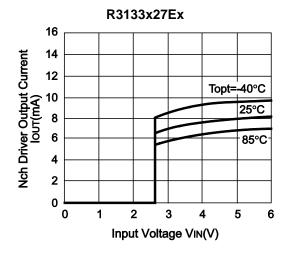
4) Nch Driver Output Current vs. Input Voltage (VDS=0.5V)

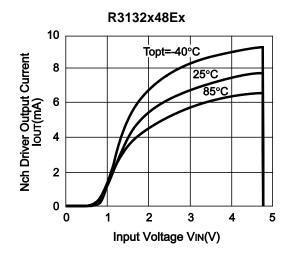


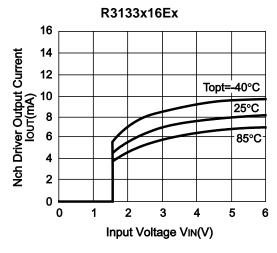


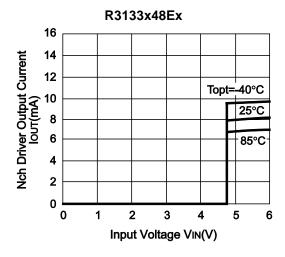




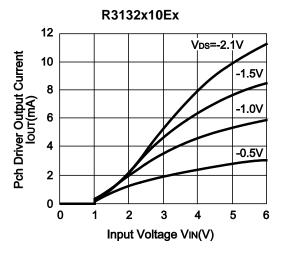


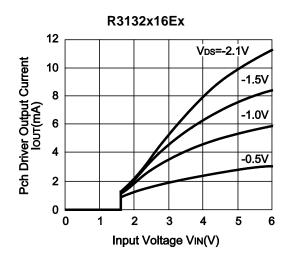


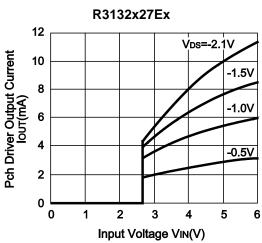


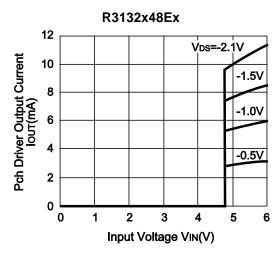


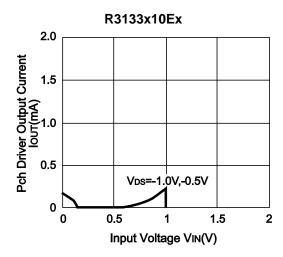
5) Pch Driver Output Current vs. Input Voltage

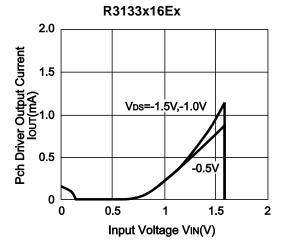


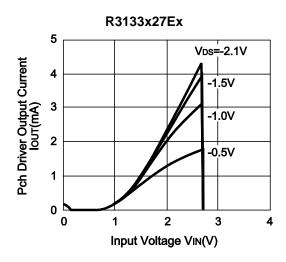


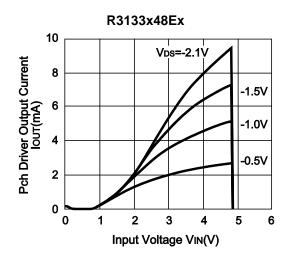




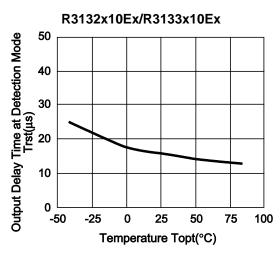


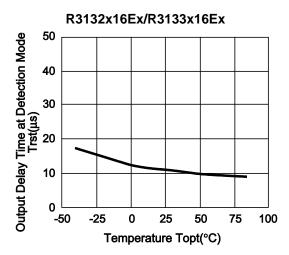


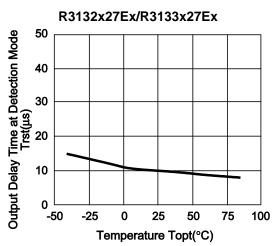


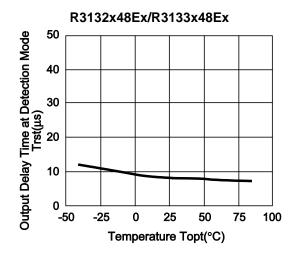


6) Output Delay Time at Detection Mode vs. Temperature

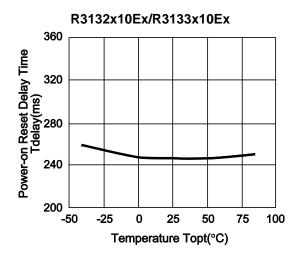


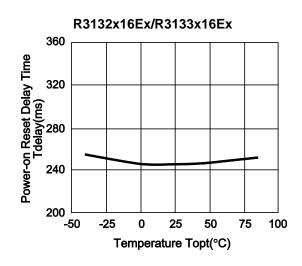


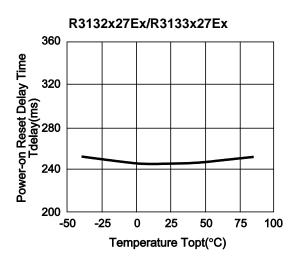


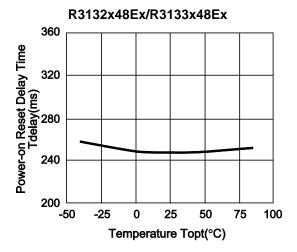


7) Power-on Reset Delay Time vs. Temperature











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